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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. KM1-003	SERIAL NO.	
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						Yes No
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)						
TT	AR		Shallow Trench Isolation Characteristics with High-Density-Plasma Chemical Vapor Deposition Gap-Fill Oxide for Deep-Submicron CMOS Technologies, Seung-Ho Lee et al., Jpn. J. Appl. Phys. Vol. 37 (1998), pp. 1222-1227.			
TT	AS		Impact of Shallow Trench Isolation on Reliability of Buried- and Surface-Chanel sub- μ m PFET, William Tonti et al., 1995 IEEE. pp. 24-29.			
TT	AT		Subbreakdown Drain Leakage Current in MOSFET, J. Chen et al., 1987 IEEE, pp.515-517.			
EXAMINER			DATE CONSIDERED			
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	AP						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
II	AR		Shallow Trench Isolation for advanced ULSI CMOS Technologies, M. Nandakumar et al, Silicon Technology Development,				
			Kilby Center, Texas Instruments, Undated, 4 pages.				
	AS						
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EXAMINER				DATE CONSIDERED			
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